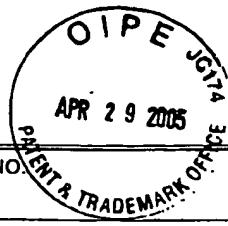




SHEET 1 OF 1

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 240669US2	PATENT & TRADEMARK OFFICE		SERIAL NO. 10/624,555
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Yukio TANIGUCHI, et al.			
				FILING DATE July 23, 2003	GROUP 1756		
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>DR</i>	AA	2004/0126674 A1	07/01/2004	Yukio TANIGUCHI, et al.			
	AB	2004/0061149 A1	04/01/2004	Masayuki JYUMONJI, et al.			
	AC	2003/0099264 A1	05/29/2003	Marcos DANTUS, et al.			
	AD	2004/0266080 A1	12/30/2004	Masayuki JYUMONJI, et al.			
	AE	2004/0142544 A1	07/22/2004	Yoshinobu KIMURA, et al.			
	AF	2004/0161913 A1	08/19/2004	Ritsuko KAWASAKI, et al.			
	AG	2002/0104750 A1	08/08/2002	Hiroshi ITO			
	AH	6,734,635 B2	05/11/2004	Masafumi KUNII, et al.			
<i>DR</i>	AI	2003/0231663 A1	12/18/2003	Tomoko OHTSUKI, et al.			
	AJ						
	AK						
	AL						
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
					YES	NO	
	AO						
	AP						
	AQ						
	AR						
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
<i>DR</i>	AW	Wen-Chang YEH, et al., "Effects of a Low-Melting-Point Underlayer on Excimer-Laser-Induced Lateral Crystallization of Si Thin-Films", Jpn. J. Appl. Phys., vol. 40, no. 5A, May 2001, pages 3096-3100					
<i>DR</i>	AX	Y. SANO, et al., "Highly Packed and Ultra-Large Si Grains Grown by a Single-Shot Irradiation of Excimer-Laser Light Pulse", Department of Physical Electronics, Tokyo Institute of Technology, 8 pages					
	AY						
	AZ					<input type="checkbox"/> Additional References sheet(s) attached	
Examiner	<i>DR D'Asasco</i>				Date Considered <i>6/30/05</i>		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

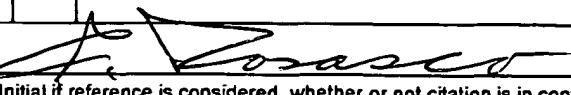


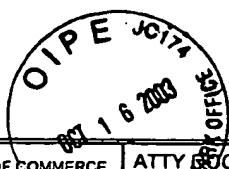
APR 29 2005

SHEET 1 OF 1

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 240669US2	SERIAL NO. 10/624,555		
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Yukio TANIGUCHI, et al.			
				FILING DATE July 23, 2003	GROUP 1756		
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
<i>DP</i>	AA	2004-0036969	02/26/04	TANIGUCHI et al.	<i>1</i>	<i>1</i>	
<i>DP</i>	AB	2004-0005744	01/08/04	TANIGUCHI et al.	<i>1</i>	<i>1</i>	
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
		AO			YES		NO
		AP					
		AQ					
		AR					
		AS					
		AT					
		AU					
		AV					
<b>OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
	AW						
	AX						
	AY						
	AZ						<input type="checkbox"/> Additional References sheet(s) attached
Examiner	<i>John Cossack</i>					Date Considered <i>6/30/05</i>	

\*Examiner: Initial If reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 240669US2		SERIAL NO. New Application	
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT		Yukio TANIGUCHI, et al.			
		FILING DATE Herewith		GROUP			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
	AO	2000-306859	11/02/00	Japan	YES	NO	<input checked="" type="checkbox"/>
	AP						
	AQ						
	AR						
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	AW	Masakiyo MATSUMURA, "PREPARATION OF ULTRA-LARGE GRAIN SILICON THIN-FILMS BY EXCIMER-LASER", Surface Science, Vol. 21, No. 5, pp. 278-287, 2000, (pgs. 34 - 43)					
	AX	M. NAKATA, et al., "TWO-DIMENSIONALLY POSITION-CONTROLLED ULTRA-LARGE GRAIN GROWTH BASED ON PHASE-MODULATED EXCIMER-LASER ANNEALING METHOD", Department of Physical Electronics, Tokyo Institute of Technology, Electrochemical Society Proceedings Vol. 2000-31, (-5- pgs)					
	AY						
	AZ					<input type="checkbox"/> Additional References sheet(s) attached	
Examiner					Date Considered <u>6/30/05</u>		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							



Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 2405589US2	SERIAL NO. 10/624,555		
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Yukio TANIGUCHI, et al.					
		FILING DATE July 23, 2003		GROUP			
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
	AO				YES	NO	
	AP						
	AQ						
	AR						
	AS						
	AT						
	AU						
<b>OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
<i>AS</i>	AV	W. YEH, et al., Jpn. J. Appl. Phys., vol. 41, Part 1, no. 4A, pages 1909-1914, "PROPOSED SAMPLE STRUCTURE FOR MARKED ENLARGEMENT OF EXCIMER-LASER-INDUCED LATERAL GRAIN GROWTH IN Si THIN FILMS", April 2002					
	AW	M. NAKATA, et al., Jpn. J. Appl. Phys., vol. 40, Part 1, no. 5A, pages 3049-3054, "A NEW NUCLEATION-SITE-CONTROL EXCIMER-LASER-CRYSTALLIZATION METHOD", May 2001					
	AX	C-H. OH, et al., Jpn. J. Appl. Phys., vol. 37, Part 2, no. 5A, pages L492 - L495, "A NOVEL PHASE-MODULATED EXCIMER-LASER CRYSTALLIZATION METHOD OF SILICON THIN FILMS", May 1, 1998					
	AY	M. MATSUMURA, et al., Thin Solid Films, vol. 337, pages 123-128, "ADVANCED EXCIMER-LASER ANNEALING PROCESS FOR QUASI SINGLE-CRYSTAL SILICON THIN-FILM DEVICES", 1999					
<i>AS</i>	AZ	M. MATSUMURA, Applied Physics, vol. 71, no. 5, pages 543-547, "EXCIMER-LASER-GROWN SILICON THIN FILMS WITH ULTRALARGE GRAINS", 2002			<input type="checkbox"/> Additional References sheet(s) attached		
Examiner <i>E. Rosasco</i>				Date Considered <i>6/30/05</i>			
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							